Unit: mm

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π–MOSV)

2SK2866

Chopper Regulator, DC-DC Converter and Motor Drive Applications

• Low drain-source ON resistance : RDS (ON) = 0.54Ω (typ.) • High forward transfer admittance : $|Y_{fs}| = 9.0 S$ (typ.)

• Low leakage current $I_{DSS} = 100 \mu A (max) (V_{DS} = 600 V)$

• Enhancement mode : $V_{th} = 2.0 \sim 4.0 \text{ V (V}_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA})$

Absolute Maximum Ratings (Ta = 25°C)

Characteri	stics	Symbol	Rating	Unit	
Drain-source voltage		V_{DSS}	600	V	
Drain-gate voltage (R	_{GS} = 20 kΩ)	V_{DGR}	600	V	
Gate-source voltage		V _{GSS}	±30	V	
Drain current	DC (Note 1)	I _D	10	Α	
Diain current	Pulse (Note 1)	I _{DP}	40	Α	
Drain power dissipatio	n (Tc = 25°C)	P_{D}	125	W	
Single pulse avalanche	e energy (Note 2)	E _{AS}	363	mJ	
Avalanche current		I _{AR}	10	Α	
Repetitive avalanche	energy (Note 3)	E _{AR}	12.5	mJ	
Channel temperature		T _{ch}	150	°C	
Storage temperature r	ange	T _{stg}	-55~150	°C	

10.3MAX. 63.6±0.2

10.3MAX. 63.6

Weight: 1.9 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R _{th (ch-c)}	1.0	°C/W
Thermal resistance, channel to ambient	R _{th (ch-a)}	83.3	°C/W

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: V_{DD} = 90 V, T_{ch} = 25°C (initial), L = 6.36 mH, R_{G} = 25 Ω , I_{AR} = 10 A

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device.

Please handle with caution.



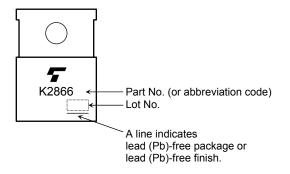
Electrical Characteristics (Ta = 25°C)

Charac	cteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	ırrent	I _{GSS}	V _{GS} = ±25 V, V _{DS} = 0 V	_	_	±10	μΑ
Gate-source bro	eakdown voltage	V (BR) GSS	$I_G = \pm 10 \mu A, V_{DS} = 0 V$	±30	_	_	V
Drain cut-off cu	rrent	I _{DSS}	V _{DS} = 600 V, V _{GS} = 0 V	_	_	100	μΑ
Drain-source br	eakdown voltage	V (BR) DSS	I _D = 10 mA, V _{GS} = 0 V	600	_	_	V
Gate threshold v	voltage	V_{th}	V _{DS} = 10 V, I _D = 1 mA	2.0	_	4.0	V
Drain-source O	N resistance	R _{DS} (ON)	V _{GS} = 10 V, I _D = 5 A	_	0.54	0.75	Ω
Forward transfe	r admittance	Y _{fs}	V _{DS} = 10 V, I _D = 5 A	3.0	9.0	_	S
Input capacitano	e	C _{iss}		_	2040	_	
Reverse transfer capacitance		C _{rss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz	_	210	_	pF
Output capacitance		Coss		_	630	_	
Switching time	Rise time	t _r	$V_{GS} = 10V$ V_{OUT} V_{OUT} V_{OUT} V_{OUT} V_{OUT} V_{OUT} V_{OUT}	_	22	_	ns
	Turn-on time	t _{on}		1	58		
	Fall time	t _f			36	_	
	Turn-off time	t _{off}	$V_{DD} = 200V$ Duty $\leq 1\%$, $t_w = 10 \mu s$	_	190	_	
Total gate charge (gate-source plus gate-drain)			_	45	_		
Gate-source charge		Q _{gs}	$V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 10 \text{ A}$		25	_	nC
Gate-drain ("miller") Charge		Q_{gd}			20	_	

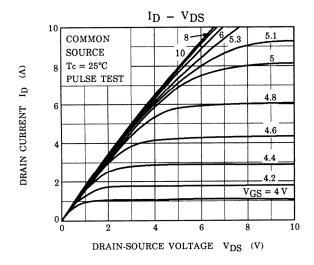
Source-Drain Ratings and Characteristics (Ta = 25°C)

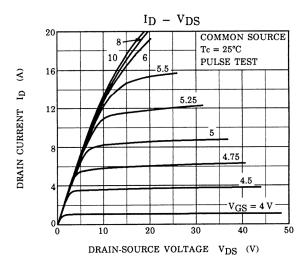
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I _{DR}	_	_	_	10	Α
Pulse drain reverse current (Note 1)	I _{DRP}	_	_	_	40	Α
Forward voltage (diode)	V _{DSF}	I _{DR} = 10 A, V _{GS} = 0 V	_	_	-1.7	V
Reverse recovery time	t _{rr}	I _{DR} = 10 A, V _{GS} = 0 V	1	1300	1	ns
Reverse recovery charge	Qrr	dl _{DR} / dt = 100 Å / μs	_	16	_	μC

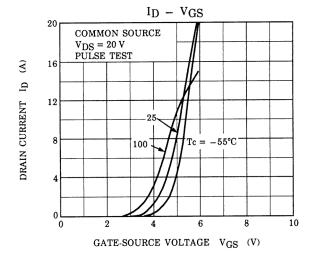
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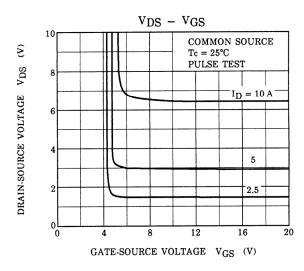


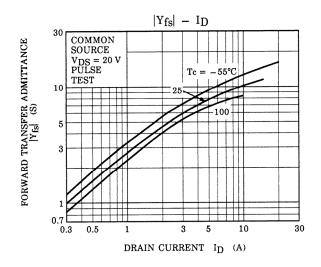
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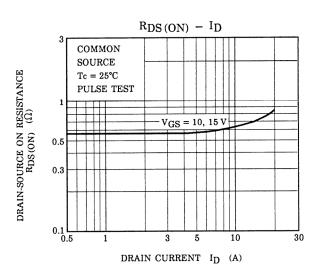




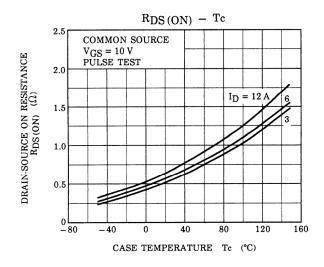


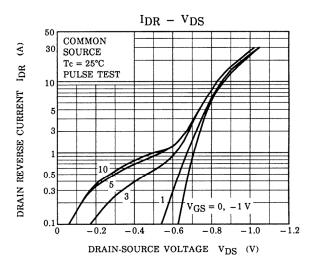


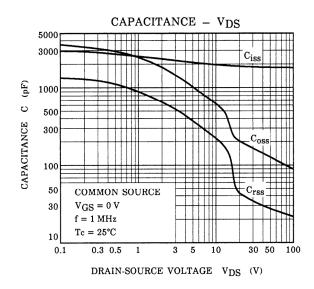


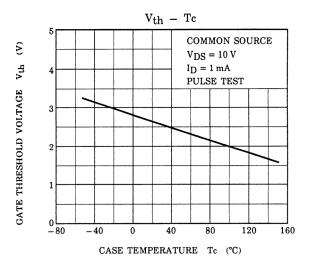


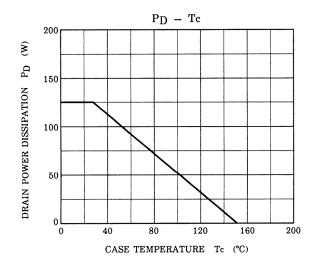
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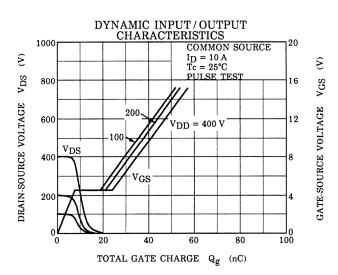


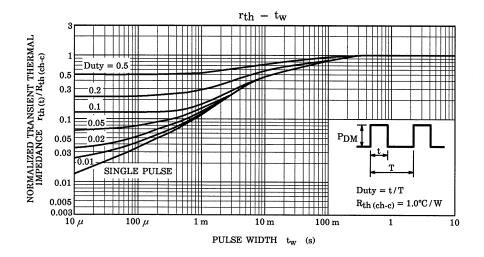


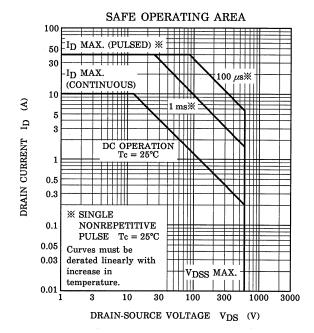


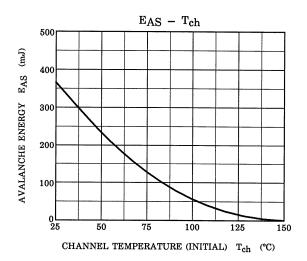


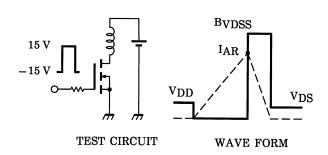












$$\begin{aligned} RG &= 25~\Omega \\ V_{DD} &= 90~V,~L = 6.36~mH \end{aligned} \qquad E_{AS} &= \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right) \end{aligned}$$

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